Silicon Diffused Power Transistor BU2508DX

GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor with an integrated damper diode in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour television receivers. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

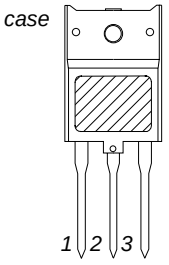
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25$ ˚C	-	45	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 4.5 A; I_B = 1.29 A	-	1.0	V
V_{CEsat}	Collector-emitter saturation voltage	I_C = 4.5 A; I_B = 1.1 A	-	5.0	V
I_{Csat}	Collector saturation current		4.5	-	A
V_F	Diode forward voltage	I_F = 4.5 A	1.6	2.0	V
t_f	Fall time	I_{Csat} = 4.5 A; $I_{B(end)}$ = 1.1 A	0.4	0.6	µs

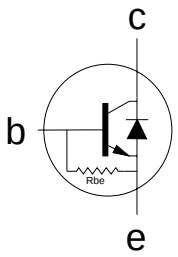
PINNING - SOT399

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	6	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	100	mA
$-I_{BM}$	Reverse base current peak value [1]		-	5	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25$ ˚C	-	45	W
T_{stg}	Storage temperature		-55	150	˚C
T_j	Junction temperature		-	150	˚C

1 Turn-off current.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}hs}$	Junction to heatsink	without heatsink compound	-	3.7	K/W
$R_{th\ j\text{-}hs}$	Junction to heatsink	with heatsink compound	-	2.8	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	35	-	K/W

ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65 % ; clean and dustfree	-	-	2500	V
C_{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	22	-	pF

STATIC CHARACTERISTICS

T_{hs} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current [2]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	1.0	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB} = 7.5 V; I_C = 0 A	140	-	390	mA
BV_{EBO}	Emitter-base breakdown voltage	I_B = 600 mA	7.5	13.5	-	V
R_{be}	Base-emitter resistance	V_{EB} = 7.5 V	-	33	-	Ω
$V_{CEOsust}$	Collector-emitter sustaining voltage	I_B = 0 A; I_C = 100 mA; L = 25 mH	700	-	-	V
V_{CEsat}	Collector-emitter saturation voltages	I_C = 4.5 A; I_B = 1.1 A	-	-	5.0	V
V_{CEsat}		I_C = 4.5 A; I_B = 1.29 A	-	-	1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 4.5 A; I_B = 1.7 A	-	-	1.3	V
h_{FE}	DC current gain	I_C = 1 A; V_{CE} = 5 V	7	13	23	
h_{FE}		I_C = 4.5 A; V_{CE} = 1 V	4	5.5	7.0	
V_F	Diode forward voltage	I_F = 4.5 A	-	1.6	2.0	V

DYNAMIC CHARACTERISTICS

T_{hs} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
C_c	Collector capacitance	I_E = 0 A; V_{CB} = 10 V; f = 1 MHz	80	-	pF
	Switching times (16 kHz line deflection circuit)	I_{Csat} = 4.5 A; $I_{B(end)}$ = 1.1 A; L_B = 6 µH; $-V_{BB}$ = 4 V; ($-dI_B/dt$ = 0.6 A/µs)			
t_s	Turn-off storage time		5.0	6.0	µs
t_f	Turn-off fall time		0.4	0.6	µs
	Switching times (38 kHz line deflection circuit)	I_{Csat} = 4.0 A; $I_{B(end)}$ = 0.9 A; L_B = 6 µH; $-V_{BB}$ = 4 V; ($-dI_B/dt$ = 0.6 A/µs)			
t_s	Turn-off storage time		4.7	5.7	µs
t_f	Turn-off fall time		0.25	0.35	µs

2 Measured with half sine-wave voltage (curve tracer).

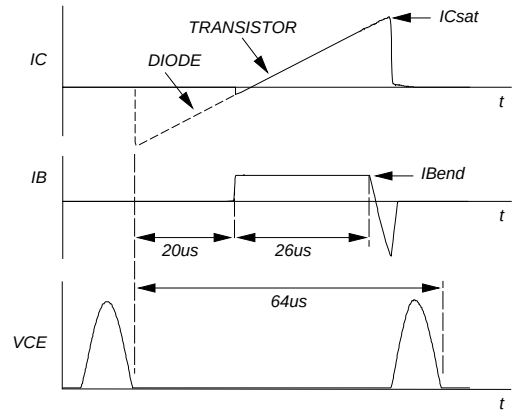


Fig.1. Switching times waveforms.

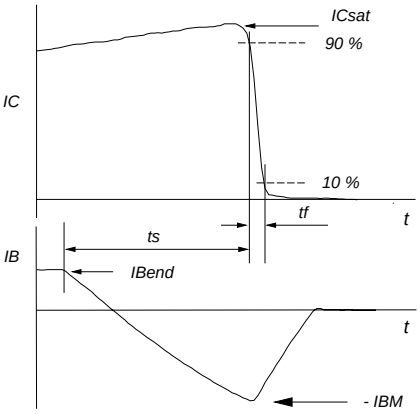


Fig.2. Switching times definitions.

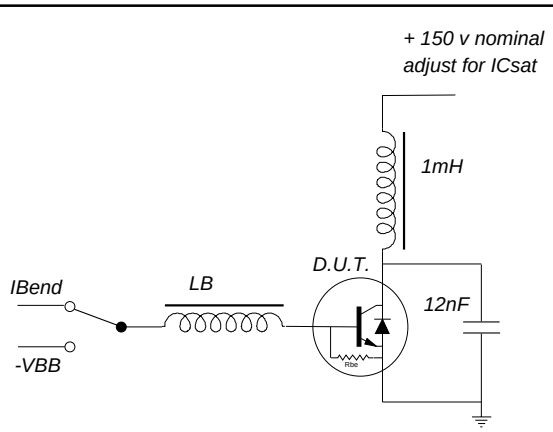


Fig.3. Switching times test circuit.

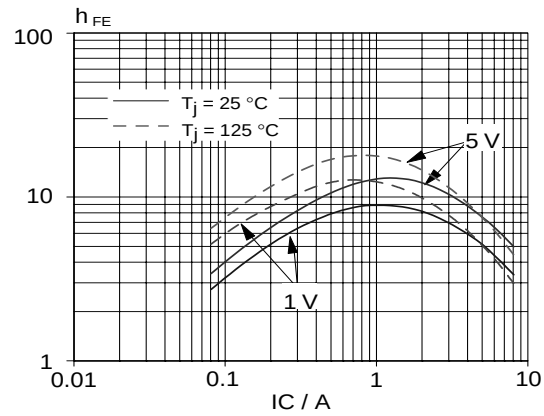


Fig.4. Typical DC current gain. h_{FE} = f (I_C) parameter V_{CE}

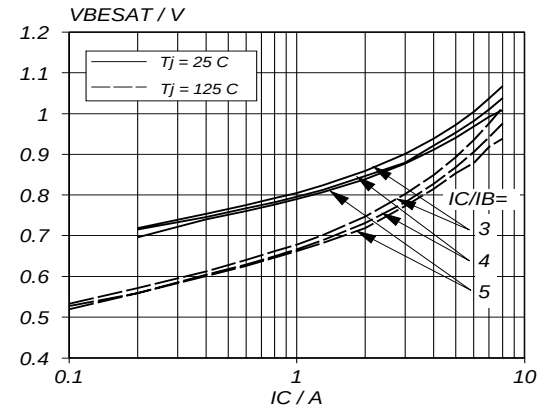


Fig.5. Typical base-emitter saturation voltage. V_{BE}sat = f (I_C); parameter I_C/I_B

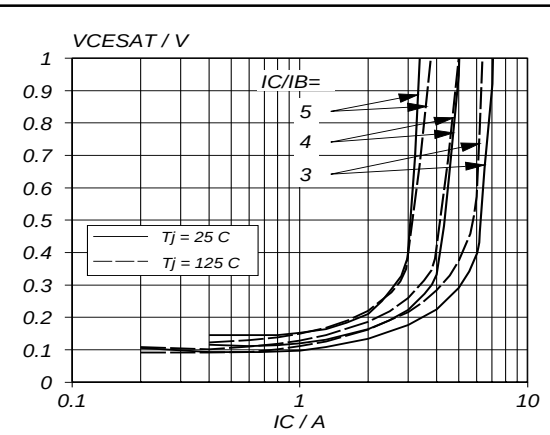


Fig.6. Typical collector-emitter saturation voltage. V_{CE}sat = f (I_C); parameter I_C/I_B

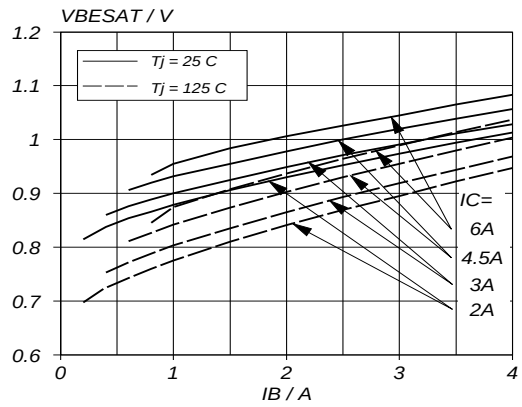


Fig.7. Typical base-emitter saturation voltage. V_{BE}sat = f (I_B); parameter I_C

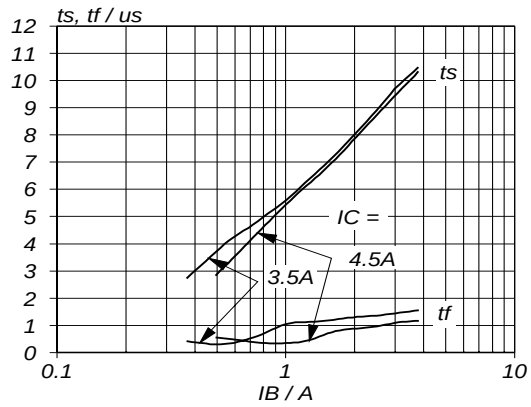


Fig.10. Typical collector storage and fall time. ts = f (I_B); tf = f (I_B); parameter I_C; T_j = 85˚C; f = 16 kHz

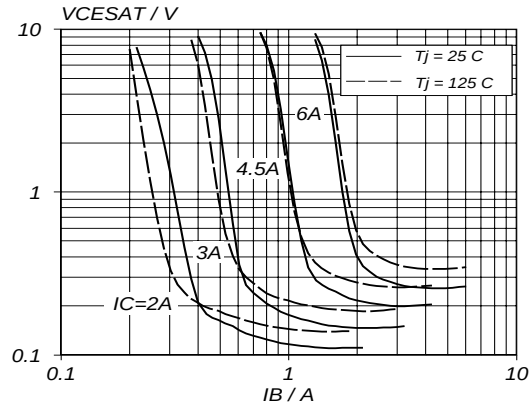


Fig.8. Typical collector-emitter saturation voltage. V_{CE}sat = f (I_B); parameter I_C

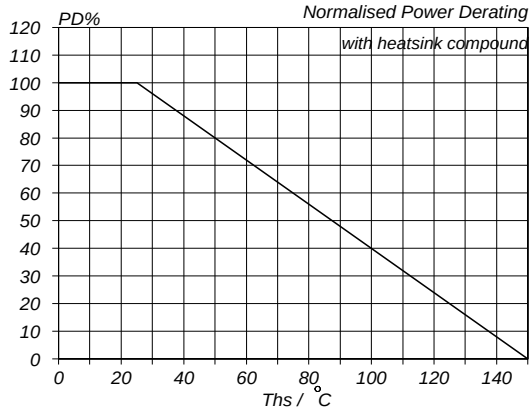


Fig.11. Normalised power dissipation. PD% = 100·P_D/$P_{D\ 25˚C}$ = f (T_{hs})

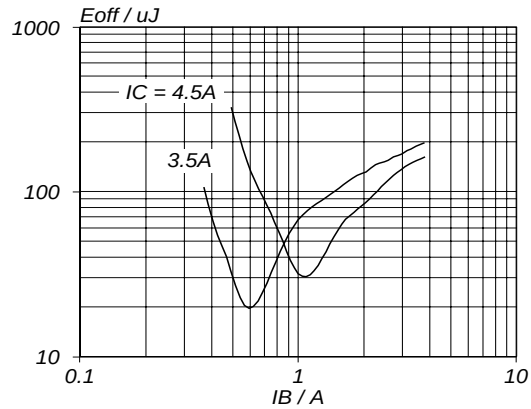


Fig.9. Typical turn-off losses. T_j = 85˚C Eoff = f (I_B); parameter I_C; f = 16 kHz

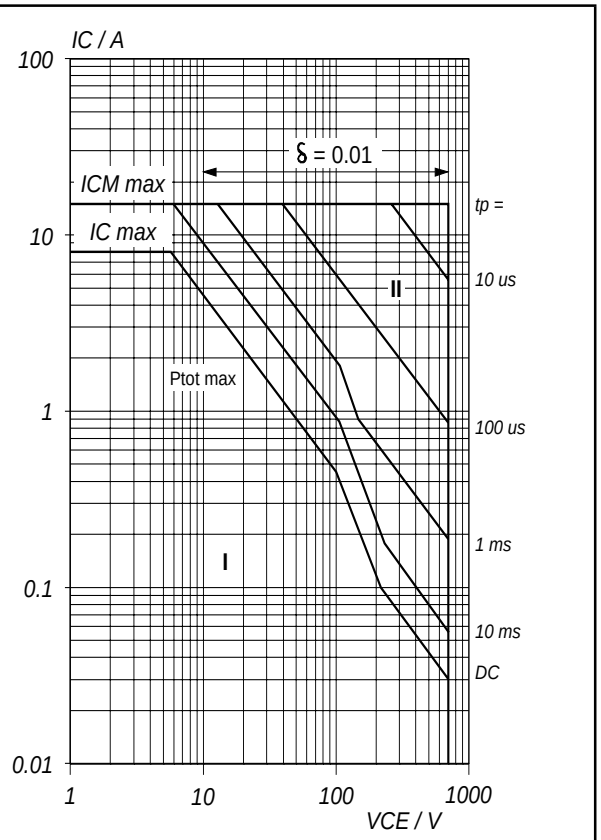


Fig.12. Forward bias safe operating area. T_{hs} = 25˚C
I *Region of permissible DC operation.*
II *Extension for repetitive pulse operation.*

NB: *Mounted with heatsink compound and 30 ± 5 newton force on the centre of the envelope.*

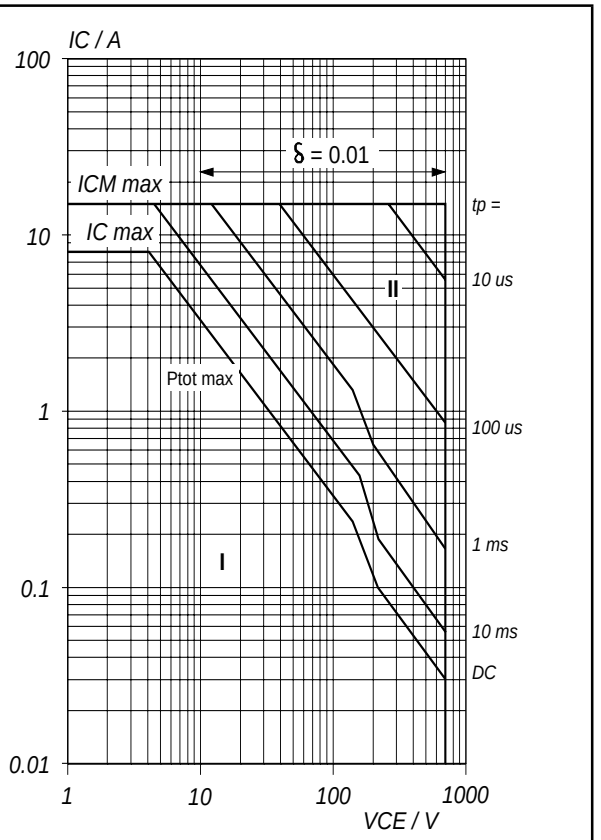


Fig.13. Forward bias safe operating area. T_{hs} = 25˚C
I *Region of permissible DC operation.*
II *Extension for repetitive pulse operation.*

NB: *Mounted without heatsink compound and 30 ± 5 newton force on the centre of the envelope.*

MECHANICAL DATA

Dimensions in mm

Net Mass: 5.88 g

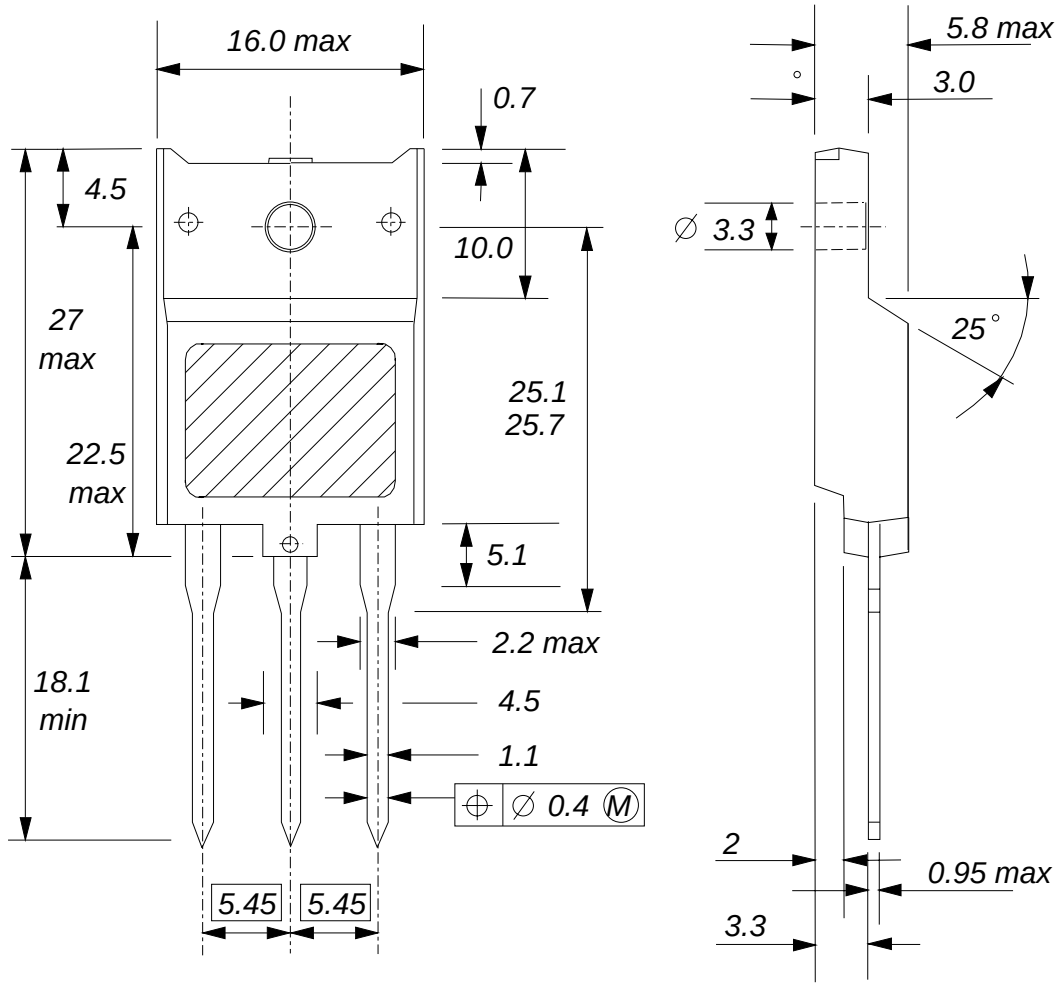


Fig.14. SOT399; The seating plane is electrically isolated from all terminals.

Notes
1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

DATA SHEET STATUS		
DATA SHEET STATUS[3]	**PRODUCT STATUS**[4]	**DEFINITIONS**
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A
Limiting values		
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

3 Please consult the most recently issued datasheet before initiating or completing a design.

4 The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.